DECLARATION AND POWER OF ATTORNEY

As a below named inventor, I hereby declare that:

My residence, post office address, and citizenship are as stated below next to my name,

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter claimed and for which a patent is sought on the invention entitled:

WING GATE TRANSISTOR FOR INTEGRATED CIRCUITS

the specification of is attached herei				
		Serial No and was amende	ed on (if applicable).
I hereby state that	I have reviewe	ed and understand the contents amended by any amendment	ents of the	above-identified
the same was not in prior to this applica	invention therec public use or or ation. I acknowle	the same was ever known or of or more than one year prior in sale in the United States of edge the duty to disclose informaccordance with title 37, Control of the control	r to this app America mormation w	plication, and that nore than one year
365(a) of any PCT the United States,	f any foreign app international app listed below and	fits under Title 35, United Staplication(s) for patent or inveblication which designated at have also identified belowing a filing date before that of	ntor's certi least one c any foreign	ificate, or Section country other than on application for
Prior Foreign App	lication(s):			
Number	Country	Day/Month/Year filed	Priority <u>Yes</u>	Claimed . <u>No</u>
I hereby claim the b application(s) listed	enefit under 35 U	JSC 119(e) of any United State	tes provisio	onal
Prior Provisional A	Application(s):			
Application Numb	er <u>Filing</u>	g Date		
I hereby claim the	benefit under T	itle 35 United States Code	Section 10	

enefit under Title 35, United States Code, Section 120 of any United States application(s), or Section 365(c) of any PCT international application designating the United States, listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States or PCT international application in the manner provided by the first paragraph of Title 35, United States Code, Section 112, I acknowledge the duty to disclose material information as defined in Title 37, Code of Federal Regulations, Section 1.56 which occurred between the filing date of the prior application and the national or PCT international filing date of this application:

Prior U.S. Application(s):

Serial No.

Filing Date

Status: Patented, Pending, Abandoned

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

I hereby revoke any previous Powers of Attorney and appoint the following attorney(s) and/or agent(s), each said individual being a member or associate of The Law Offices of Mikio Ishimaru or being employed by Chartered Semiconductor Manufacturing Ltd.:

Mikio Ishimaru

Reg. No. 27,449

William D. Zahrt II

Reg. No. 26,070

for so long as they remain with such law offices or company with full power of substitution and revocation, to prosecute this application and to transact in connection therewith all business in the Patent and Trademark Office and before competent International Authorities; said appointment to be to the exclusion of myself and my other attorney(s); and all future correspondence should be addressed to:

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